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(71) Applicant (for all designated States except US): **BOREALIS TECHNICAL LIMITED [US/US]; 23545 N.W. Skyline Boulevard, North Plains, OR 97133-9204 (US).**

(72) Inventors; and

(75) Inventors/Applicants (for US only): **MARTSINOVSKY, Artemi [RU/RU]; 1B-19 Maily Prospects PS, St.Petersburg**

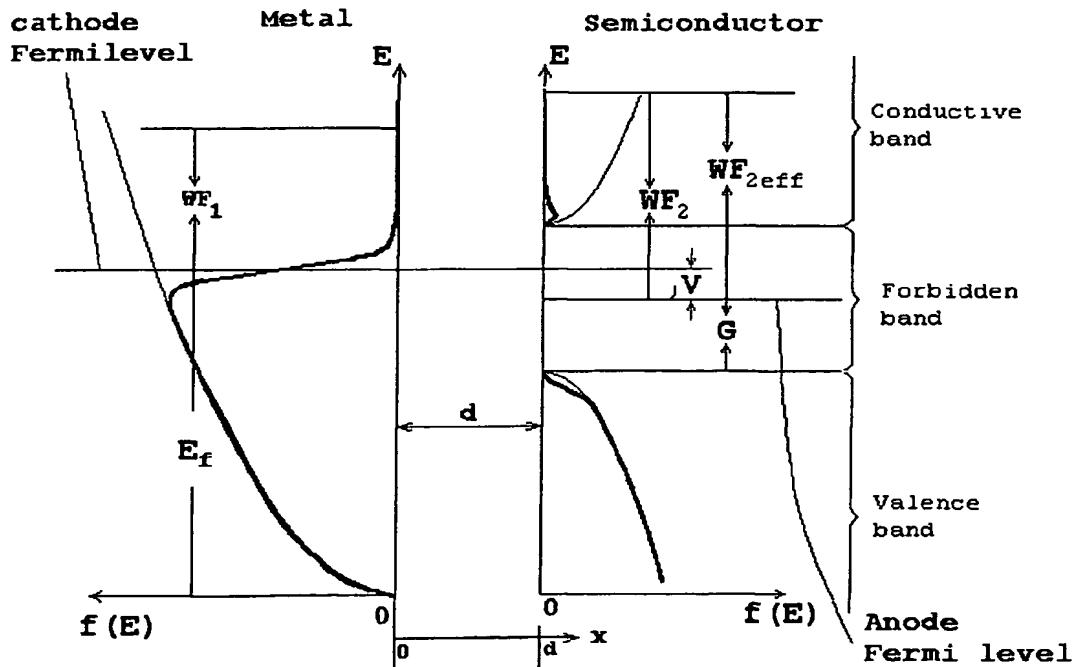
(74) Agent: **BOREALIS TECHNICAL LIMITED; Rodney T. Cox, Chairman and CEO, 23545 NW Skyline Blvd, North Plains, OR 97133-9204 (US).**

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(54) Title: TUNNELING GAP DIODES



(57) Abstract: The present invention discloses a tunneling diode having a band gap material as the collector. This increases the tunneling of electrons having greater energy than the Fermi level from emitter to collector, leading to an increase in the efficiency of heat pumping or power generation by the diode. This approach also reduces back tunneling of electrons from collector to emitter.



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